

U.S. Application No. 10/014,563

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forming at least one first MEMS component by patterning the single crystal silicon layer;
forming at least one second MEMS component by patterning the polysilicon; and
depositing at least one layer of polysilicon on the patterned single crystal silicon.

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24. (AMENDED) The method of claim 23 wherein the at least one first MEMS component is a mirror retained by the hinge.

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27. (AMENDED) A MEMS formation method including:
providing a SOI wafer including a single crystal silicon layer attached to an insulator layer;
forming at least one first MEMS component by patterning the single crystal silicon layer;
depositing at least one layer of polysilicon on the patterned single crystal silicon; and
wherein forming at least one first MEMS component includes forming a deflecting mirror. D

Sub C3
30. (AMENDED) A MEMS device comprising:
at least one single crystal silicon component bonded to an insulator that rests on a handle wafer;
a polysilicon hinge derived from a layer of polysilicon applied over the at least one single crystalline component; and
at least one polysilicon component derived from a layer of polysilicon applied over the at least one single crystalline silicon component. B4

31. (AMENDED) The MEMS device of claim 30 wherein the at least one single crystal silicon component comprises a deflecting mirror retained by the hinge. 13

32. (AMENDED) The MEMS device of claim 31 wherein the at least one polysilicon component is attached to and retained by the hinge. sub D

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D 34. (AMENDED) The MEMS device of claim 30 wherein the at least one polysilicon component is attached to and retained by the hinge.

35. (AMENDED) A MEMS device comprising:

at least one single crystal silicon component bonded to an insulator that rests on a handle wafer; and

at least one polysilicon component derived from a layer of polysilicon applied over the at least one single crystalline silicon component ;

a recess in the handle wafer aligned with the at least one single crystal silicon component; and

a semiconductor light emitter mounted in the recess and oriented to emit a light beam at the single crystal silicon component.